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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 09/519,165

BOX RCE

Filing Date: March 6, 2000

Examiner: W. Watkins, III

Inventors: David W. Sherrer et al.

Art Unit: 1772

Title: Single Mask Lithographic  
Process For Patterning  
Multiple Types Of Surface  
FeaturesAssistant Commissioner for Patents  
Washington, DC 20231FAX RECEIVED  
MAY 01 2003  
GROUP 1700AMENDMENT

Sir:

In response to the final Official Action issued September 25, 2002, applicants submit the following amendments and remarks:

IN THE CLAIMS:

Please amend the claims as follows:

1. (Amended) A method for fabricating the etched optoelectronic apparatus of claim 1, comprising the steps of:
- a) providing a semiconductor substrate with a top surface and a planar dielectric layer on the top surface;
  - b) forming a patterned metal layer on the dielectric layer, wherein the patterned metal layer has a metal edge;
  - c) forming a patterned resist layer on the dielectric layer and patterned metal layer, wherein the resist layer has a resist edge that is located on top of the metal layer such that the dielectric layer has an exposed area defined by the metal edge;
  - d) etching away the dielectric layer from the exposed area;
  - e) etching the semiconductor substrate where the dielectric layer is etched away in step (d), thereby forming a pit; and
  - f) placing an optical element into the pit.